

# Refine Search

## Search Results -

Terms	Documents
L7 and (plasma near3 treatment)	5

Database:

- US Pre-Grant Publication Full-Text Database
- US Patents Full-Text Database
- US OCR Full-Text Database
- EPO Abstracts Database
- JPO Abstracts Database
- Derwent World Patents Index
- IBM Technical Disclosure Bulletins

Search:

L8

Refine Search

Recall Text

Clear

Interrupt

## Search History

DATE: Thursday, April 14, 2005   [Printable Copy](#)   [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ</i>			
<u>L8</u>	L7 and (plasma near3 treatment)	5	<u>L8</u>
<u>L7</u>	L5 and (plasma same amorphous same polysilicon)	28	<u>L7</u>
<u>L6</u>	L5 and plasma	233	<u>L6</u>
<u>L5</u>	L4 and island	273	<u>L5</u>
<u>L4</u>	L3 and amorphous and polysilicon	455	<u>L4</u>
<u>L3</u>	L1 and threshold voltage	770	<u>L3</u>
<u>L2</u>	L1 and threshhold voltage	0	<u>L2</u>
<u>L1</u>	low temperature near8 (thin film transistor or TFT)	2289	<u>L1</u>

END OF SEARCH HISTORY